



Phase Control Thyristors (Stud Version), 180 A



TO-209AB (TO-93)

FEATURES

- Hermetic glass-metal seal
- International standard case TO-209AB (TO-93)
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRODUCT SUMMARY	
$I_{T(AV)}$	180 A
V_{DRM}/V_{RRM}	400 V, 800 V, 1000 V
V_{TM}	1.35 V
I_{GT}	65 mA
T_J	-40 °C to 125 °C
Package	TO-209AB (TO-93)
Diode variation	Single SCR

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		180	A
	T_C	80	°C
$I_{T(RMS)}$		285	A
I_{TSM}	50 Hz	3800	
	60 Hz	4000	
I^2t	50 Hz	72	kA ² s
	60 Hz	66	
V_{DRM}/V_{RRM}		400 to 1000	V
t_q	Typical	100	µs
T_J		-40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
PART NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-180RKI VS-181RKI	40	400	500	30
	80	800	900	
	100	1000	1100	



ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave		180	A
				80	°C
Maximum RMS on-state current	I_{RMS}	DC at 79 °C case temperature		285	A
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reappplied	3800	
		t = 8.3 ms		4000	
		t = 10 ms	100 % V_{RRM} reappplied	3500	
		t = 8.3 ms		3660	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reappplied	72	kA ² s
		t = 8.3 ms		66	
		t = 10 ms	100 % V_{RRM} reappplied	61	
		t = 8.3 ms		56	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reappplied		720	kA ² √s
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$, $T_J = T_J$ maximum		0.83	V
High level value of threshold voltage	$V_{T(TO)2}$	(I > $\pi \times I_{T(AV)}$, $T_J = T_J$ maximum		0.89	
Low level value of on-state slope resistance	r_{t1}	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$, $T_J = T_J$ maximum		0.92	mΩ
High level value of on-state slope resistance	r_{t2}	(I > $\pi \times I_{T(AV)}$, $T_J = T_J$ maximum		0.81	
Maximum on-state voltage	V_{TM}	$I_{pk} = 570$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine pulse		1.35	V
Maximum holding current	I_H	$T_J = 25$ °C, anode supply 12 V resistive load		600	mA
Typical latching current	I_L			1000	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dI/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}		300	A/μs
Typical delay time	t_d	Gate current 1 A, $dI_g/dt = 1$ A/μs $V_d = 0.67$ % V_{DRM} , $T_J = 25$ °C		1.0	μs
Typical turn-off time	t_q	$I_{TM} = 50$ A, $T_J = T_J$ maximum, dI/dt = 10 A/μs, $V_R = 100$ V, dV/dt = 20 V/μs		100	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}		500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied		30	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		10		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$		2.0		
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		3.0		A
Maximum peak positive gate voltage	$+V_{GM}$			20		V
Maximum peak negative gate voltage	$-V_{GM}$			5.0		
DC gate current required to trigger	I_{GT}	$T_J = -40$ °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	130	-	mA
		$T_J = 25$ °C		65	150	
		$T_J = 125$ °C		35	-	
DC gate voltage required to trigger	V_{GT}	$T_J = -40$ °C		2.0	-	V
		$T_J = 25$ °C		1.2	2.5	
		$T_J = 125$ °C		0.9	-	
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode to cathode applied	10		mA
DC gate voltage not to trigger	V_{GD}			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T_J		-40 to 125	°C
Maximum storage temperature range	T_{Stg}		-40 to 150	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.15	K/W
Maximum thermal resistance, junction to ambient	R_{thCS}	Mounting surface, smooth, flat and greased	0.04	
Mounting force, ± 10 %		Non-lubricated threads	31 (275)	N · m (lbf · in)
		Lubricated threads	24.5 (210)	
Approximate weight			280	g
Case style		See dimensions - link at the end of datasheet	TO-209AB (TO-93)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.050	0.032	$T_J = T_J$ maximum	K/W
120°	0.063	0.059		
90°	0.080	0.082		
60°	0.118	0.124		
30°	0.225	0.228		

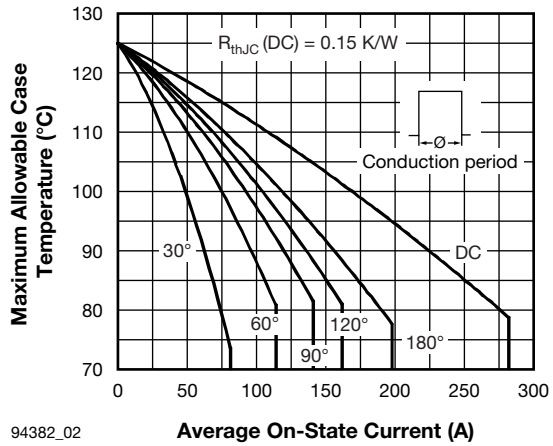
Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



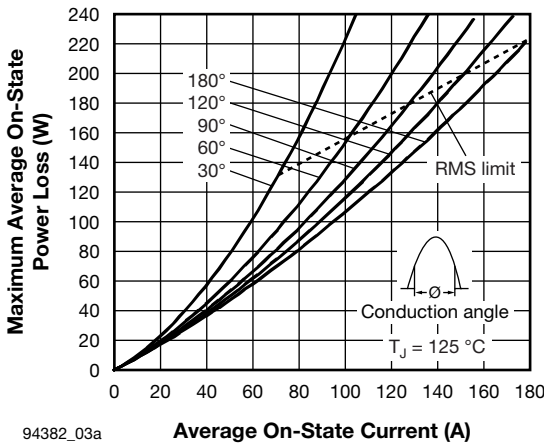
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Fig. 1 - Current Ratings Characteristics

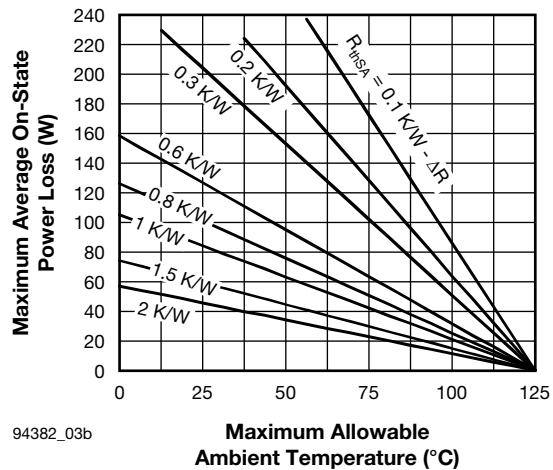


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Fig. 2 - Current Ratings Characteristics

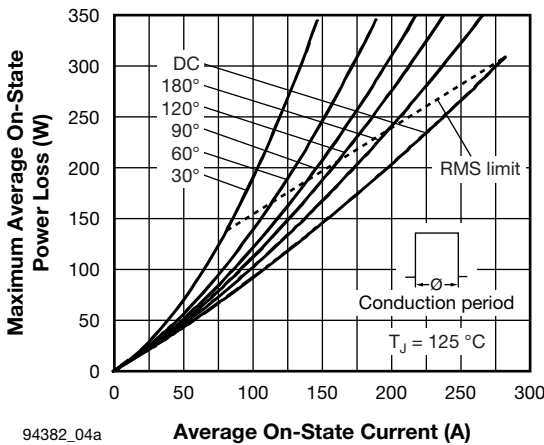


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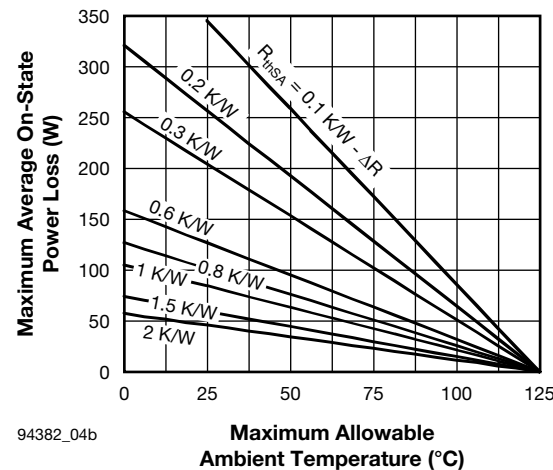


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Fig. 3 - On-State Power Loss Characteristics



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94382_04b

Fig. 4 - On-State Power Loss Characteristics



Fig. 5 - Maximum Non-Repetitive Surge Current



Fig. 6 - Maximum Non-Repetitive Surge Current



Fig. 7 - On-State Voltage Drop Characteristics



Fig. 8 - Thermal impedance Z_{thJC} Characteristics



Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	18	1	RKI	100	PbF
	(1)	(2)	(3)	(4)	(5)	(6)

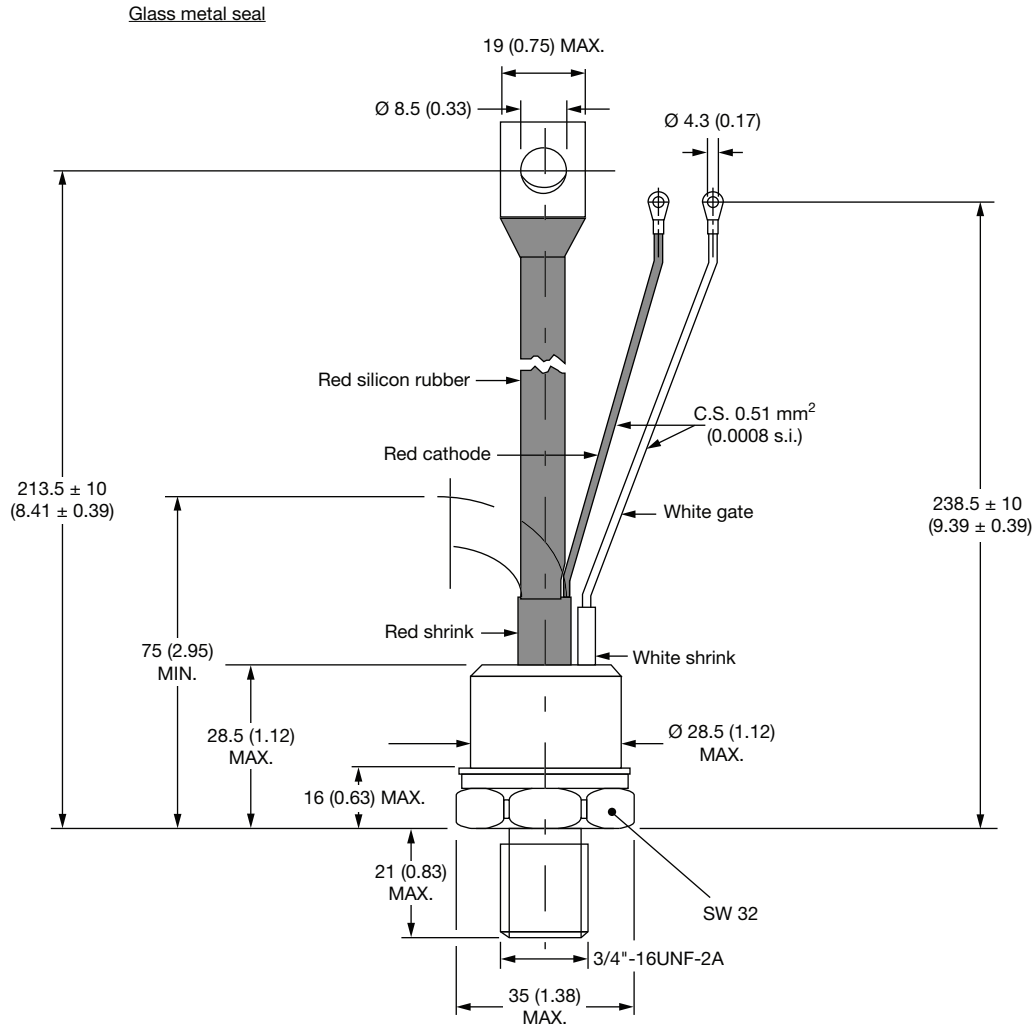
- 1** - Vishay Semiconductors product
- 2** - $I_{T(AV)}$ rated average output current (rounded/10)
- 3** -
 - 0 = Eyelet terminals (gate and auxiliary cathode leads)
 - 1 = Fast-on terminals (gate and auxiliary cathode leads)
- 4** - Thyristor
- 5** - Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- 6** -
 - None = Standard production
 - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS

Dimensions	www.vishay.com/doc?95077
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TO-209AB (TO-93)

DIMENSIONS in millimeters (inches)





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- Подбор аналогов;
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